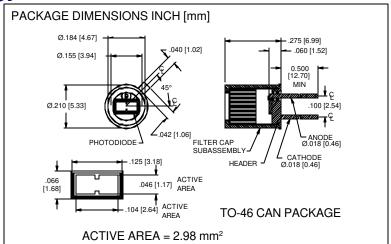
**PHOTONIC** Silicon Photodiode, Filter Combination Photovoltaic **DETECTORS INC.** (center wavelength 850 nm) Type PDI-V485-46





RESPONSIVITY (A/W)

#### **FEATURES**

- 850 nm CWL
- 10 nm FWHM
- · Large active area

#### **DESCRIPTION**

The **PDI-V485-46** is a silicon, PIN planar diffused, photodiode with a narrow band interferance filter. The detector filter combination has a narrow 10 nm half bandwidth designed for low noise photovoltaic applications.

tions. Packaged in a TO-46 metal can.

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

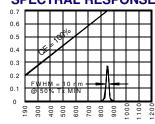
SYMBOL	PARAMETER	MIN	MAX	UNITS
$V_{BR}$	Reverse Voltage		75	V
T <sub>stg</sub>	Storage Temperature	-20	+85	°C
То	Operating Temperature Range	-15	+70	°C
Ts	Soldering Temperature*		+240	°C
I <sub>L</sub>	Light Current		0.5	mA

<sup>\*1/16</sup> inch from case for 3 secs max

## **APPLICATIONS**

- Spectrophotometry
- Chemistry instrumentation
- Liquid chromatography

# **SPECTRAL RESPONSE**



WAVELENGTH (nm)

## **ELECTRO-OPTICAL CHARACTERISTICS** (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current***	H = 100 fc, 2850 K	35	40		μΑ
ΙD	Dark Current	H = 0, V <sub>R</sub> = 10 V		150	300	pА
Rsh	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	1.0	6		GΩ
TC Rsh	Rsн Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		%/℃
Cı	Junction Capacitance	H = 0, V <sub>R</sub> = 0 V**		340		pF
CWL	Center Wavelength	(CWL, $\lambda$ o) +/- 2 nm		850		nm
HBW	Half Bandwidth	(FWHM)		10		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 µuA	30	50		V
N EP	Noise Equivalent Power	V <sub>R</sub> = 10 mV @ Peak		5x10 <sup>-14</sup>		W/ √Hz
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 0 V		450		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.\*\*f = 1 MHz, \*\*\*without filter [FORM NO. 100-PDI-V485-46 REV N/C]